

The invention relates to the processes for introduction of a "guest" component with a layered crystalline structure. The proposed process consists in a laser radiation at an angle of $90^\circ \pm 10^\circ$ to the "guest" component film plane applied to one of the example faces which is parallel to the crystallographic axis C. And the introduced intercalant (admixture) quantity is adjusted by the applied film thickness, a value of radiation energy density in the pulse and by the quantity of laser pulses.